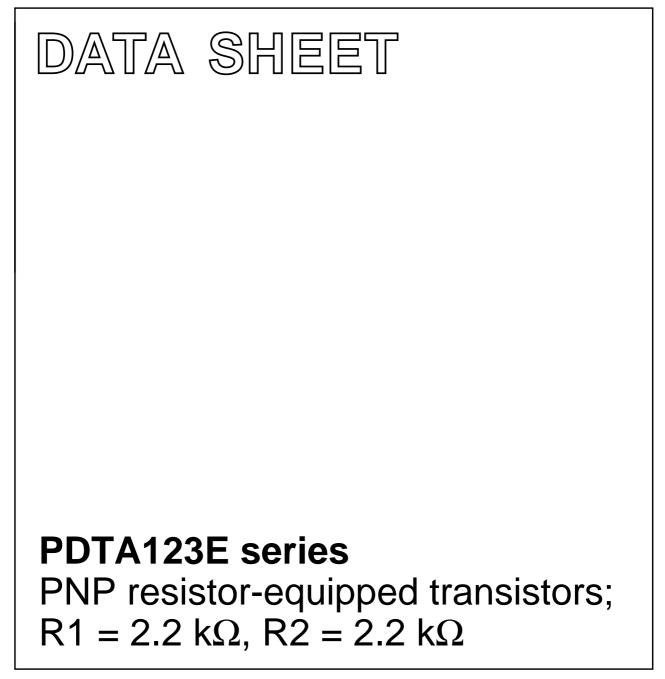
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2004 Apr 07 2004 Aug 02



PDTA123E series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

PRODUCT OVERVIEW

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-	-50	V
lo	output current (DC)	-	-100	mA
R1	bias resistor	2.2	_	kΩ
R2	bias resistor	2.2	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT	
	PHILIPS	EIAJ			
PDTA123EE	SOT416	SC-75	5C	PDTC123EE	
PDTA123EEF	SOT490	SC-89	6C	PDTC123EEF	
PDTA123EK	SOT346	SC-59	42	PDTC123EK	
PDTA123EM	SOT883	SC-101	F7	PDTC123EM	
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES	
PDTA123ET	SOT23	_	*21 ⁽¹⁾	PDTC123ET	
PDTA123EU	SOT323	SC-70	*42 ⁽¹⁾	PDTC123EU	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TYPE NUMBER			DESCRIPTION		
PDTA123ES	$ \begin{array}{c} 1 \\ 1 \\ 2 \\ 3 \\ \end{array} $ $ \begin{array}{c} R1 \\ R2 \\ 3 \\ \end{array} $ $ \begin{array}{c} R1 \\ R2 \\ 3 \\ \end{array} $ $ \begin{array}{c} R1 \\ R2 \\ 3 \\ \end{array} $	PIN 1 2 3	base collector emitter		
PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU	$\begin{array}{c} & 3 \\ 1 \\ 1 \\ Top view \end{array}$	1 2 3	base emitter collector		
PDTA123EM	2 1 Bottom view 3 1 R1 R2 MDB267 3 MDB267	1 2 3	base emitter collector		

PDTA123E series

ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
	NAME	DESCRIPTION	VERSION		
PDTA123EE	-	plastic surface mounted package; 3 leads	SOT416		
PDTA123EEF	-	plastic surface mounted package; 3 leads	SOT490		
PDTA123EK	 plastic surface mounted package; 3 leads SC 		SOT346		
PDTA123EM	 leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm 		SOT883		
PDTA123ES	-	plastic single-ended leaded (through hole) package; 3 leads	SOT54		
PDTA123ET	-	plastic surface mounted package; 3 leads	SOT23		
PDTA123EU	_	plastic surface mounted package; 3 leads	SOT323		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	– –50 V		V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		-	-12	V
lo	output current (DC)		-	-100	mA
I _{CM}	peak collector current – – –100		-100	mA	
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature -65 +150		°C		

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

PDTA123E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

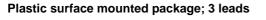
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μA
		$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-2	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -20 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	-	-	-150	mV
V _{i(off)}	input-off voltage	$I_{C} = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	-	-1.2	-0.5	V
V _{i(on)}	input-on voltage	$I_{C} = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2	-1.6	-	V
R1	input resistor		1.54	2.2	2.86	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	-	-	3	pF

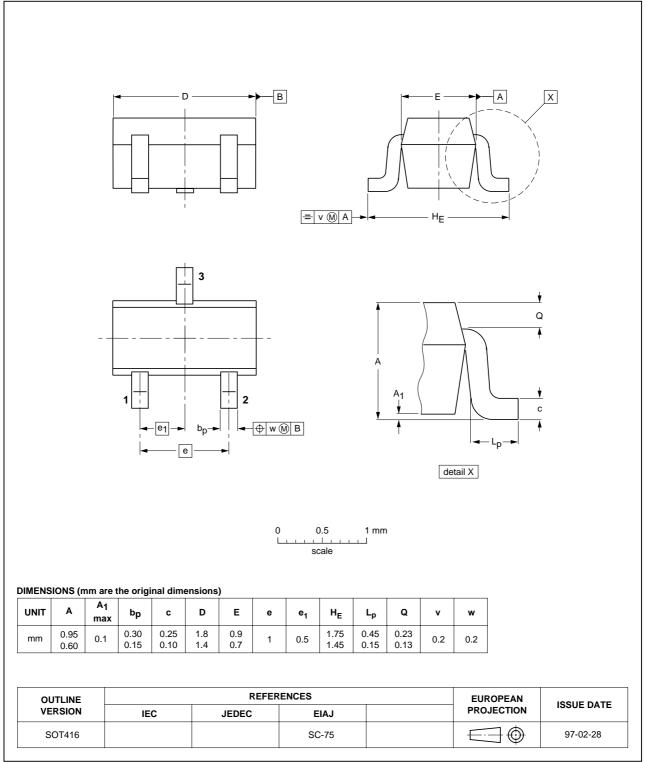
SOT416

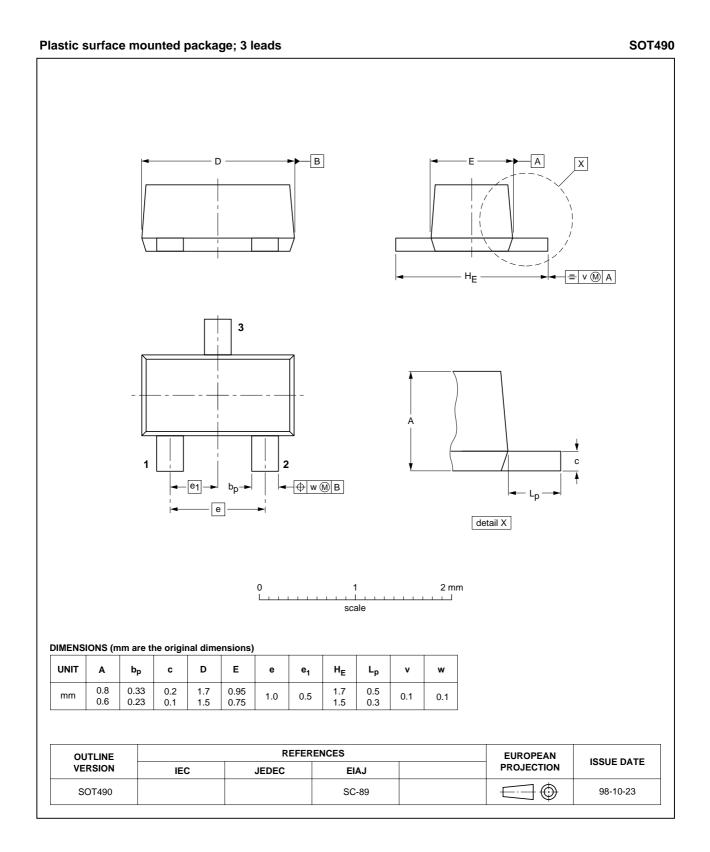
PDTA123E series

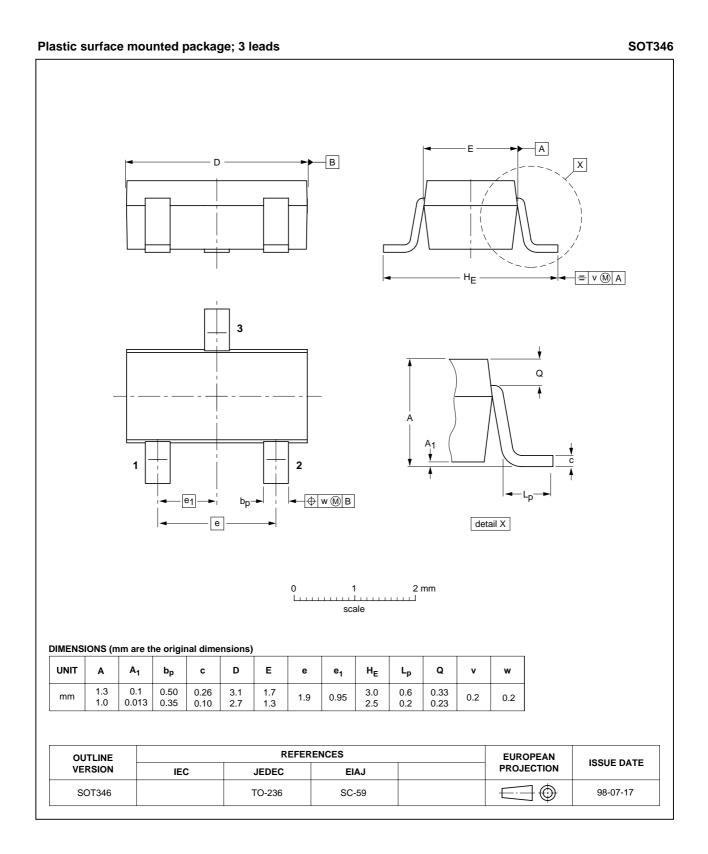
PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

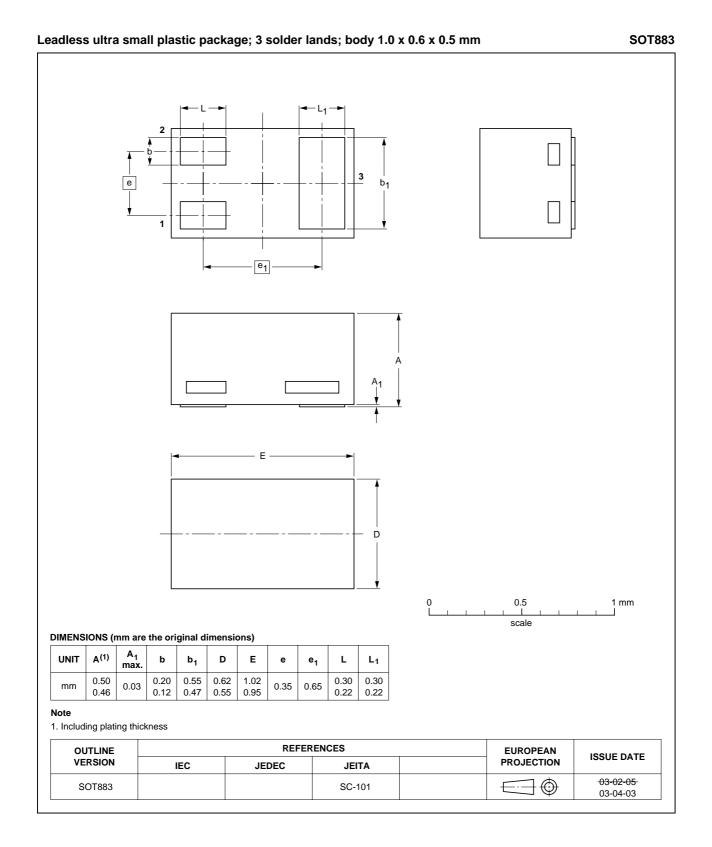
PACKAGE OUTLINES

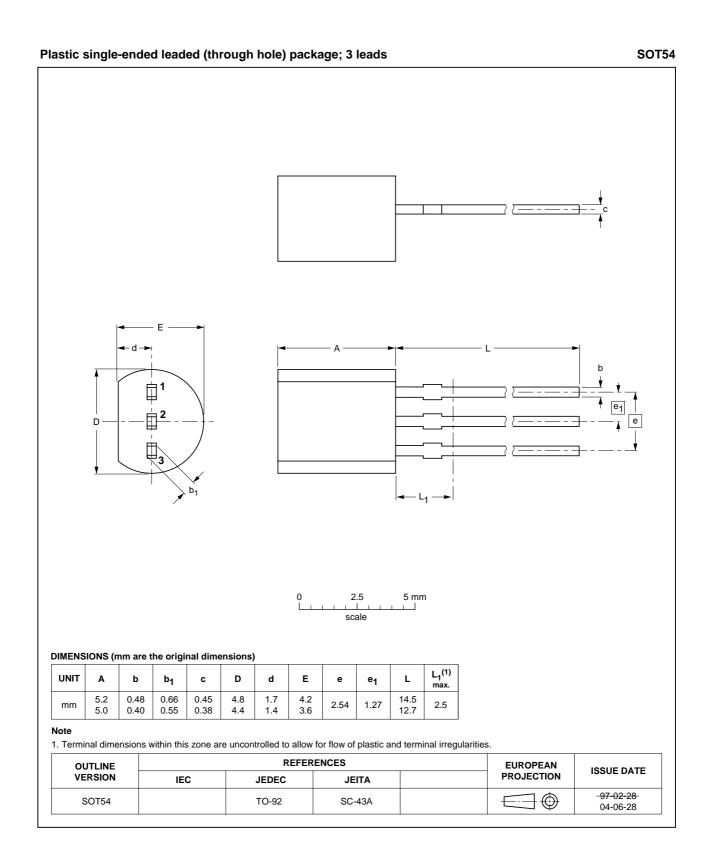


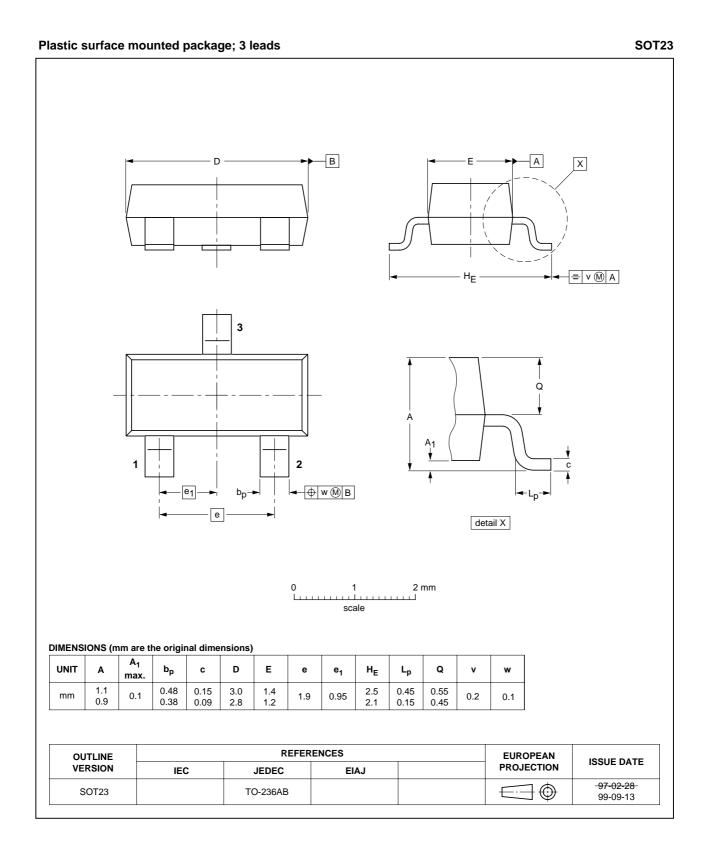


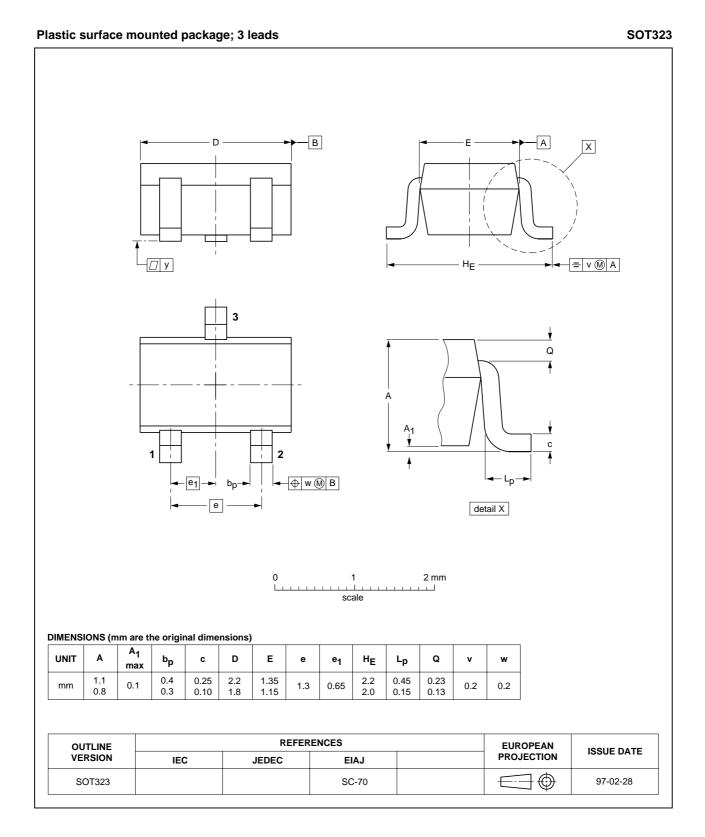












PDTA123E series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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